

### isc Silicon PNP Power Transistor

## 2SA1078

### DESCRIPTION

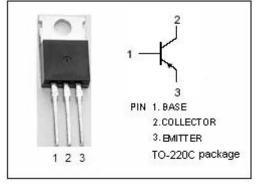
- Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= -120V(Min.)
- Good Linearity of h<sub>FE</sub>
- Wide Area of Safe Operation
- Complement to Type 2SC2528
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

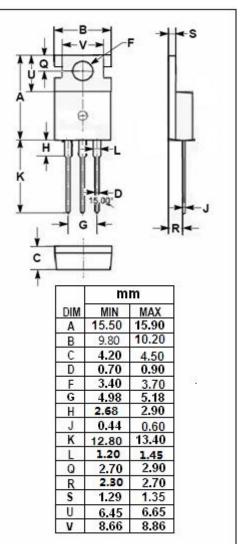
### APPLICATIONS

- · High frequency power amplifiers
- Audio power amplifiers and drivers

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>сво</sub>	Collector-Base Voltage	-120	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-120	
$V_{\text{EBO}}$	Emitter-Base Voltage	ase Voltage -5	
lc	Collector Current-Continuous	-2	А
Pc	Collector Power Dissipation @Tc=25°C	25	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C





isc website: <u>www.iscsemi.com</u>

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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	Ic= -1mA; R <sub>BE</sub> = ∞	-120			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -1 μ Α; I <sub>E</sub> = 0	-120			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -1 μ A; I <sub>C</sub> = 0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -0.7A; I <sub>B</sub> = -0.07A			-1.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -0.7A; V <sub>CE</sub> = -5V			-1.7	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -120V; I <sub>E</sub> = 0			-1	μA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -120V; I <sub>B</sub> = 0			-100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-1	μA
h <sub>FE-1</sub>	DC Current Gain	Ic= -0.3A; Vce= -5V	60		350	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -0.7A; V <sub>CE</sub> = -5V	50			
Сов	Outut Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f= 1.0MHz		100		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -10V; f=10MHz		140		MHz

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